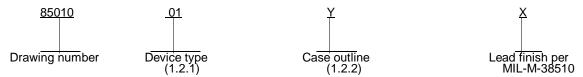
									REVIS	SIONS										
LTR	DESCRIPTION									DATE (YR-MO-DA)			DA)	APPROVED						
С	Convert drawing to new boiler plate. Corrected vendo similar part number for vendor CAGE 34335. Editorial changes throughout.									W.Heckman										
CURREI	NT C	AG	E C	ODE	≣ 67	268														
REV	С	С	С	С																
SHEET	35	36	37	38																
REV	С	С	С	С	С	С	С	С	С	С	С	С	С	С	С	С	С	С	С	С
SHEET	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34
REV STATU OF SHEET	S			RE\	/		С	С	С	С	С	С	С	С	С	С	С	С	С	С
				SHE	EET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A					PARED ry Tuns						DEF	ENSI	E ELE					ENTE	₹	
	ITAR	Y	)		CKED H. Noh					DAYTON, OHIO 45444										
THIS DRAWII	NG IS A ISE BY	DRAWING  THIS DRAWING IS AVAILABLE FOR USE BY ALL			APPROVED BY William K. Heckman				MICROCIRCUIT, 16-BIT N-CHANNEL MICRO- PROCESSOR, MONOLITHIC SILICON											
FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE				DRAWING APPROVAL DATE 18 OCTOBER 1985						FRC	JCES:	,								
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### 1. SCOPE

- 1.1 <u>Scope</u>. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".
  - 1.2 Part number. The complete part number shall be as shown in the following example:



1.2.1 <u>Device types</u>. The device types shall identify the circuit function as follows:

Device type	Generic number	<u>Frequency</u>	<u>Circuit</u>
1	M80186 8 Mhz	16-bitN-channelmic	roprocessor
02	M80186 6 Mhz	16-bit N-channel mi	icroprocessor

1.2.2 <u>Case outlines</u>. The case outlines shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter	Case outline
Y Z	68-terminal ceramic quad package (see figure 1) P-AC (1.160" X 1.160"), pin grid array package

1.3 Absolute maximum ratings.

Voltage on any pin (referenced to GND) Storage temperature range	-1.0 V dc to +7.0 V dc -65° C to +150° C -3 W 12° C/W See MIL-M-38510, appendix C +150° C +260° C
--	---

1.4 Recommended operating conditions.

Supply voltage range (V <sub>CC</sub> ): Device type 01	
Device type 01	4.75 V dc to 5.25 V dc
Device type 02	4.75 V dc to 5.25 V dc
Frequency of operation:	
Device type 01	8 MHz
Device type 02	6 MHz
Case operating temperature range (T <sub>C</sub> )	-55° C to +125° C

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#### 2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standard, and bulletin</u>. Unless otherwise specified, the following specification, standard, and bulletin of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

**SPECIFICATION** 

**MILITARY** 

MIL-M-38510 - Microcircuits, General Specification for.

**STANDARD** 

**MILITARY** 

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

**BULLETIN** 

**MILITARY** 

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

(Copies of the specification, standard, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

#### 3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
  - 3.2.1 Terminal connections. The terminal connections shall be as specified on figure 2.
  - 3.2.2 Functional block diagram. The functional block diagram shall be as specified on figure 3.
  - 3.2.3 Case outlines. The case outlines shall be in accordance with 1.2.2 herein.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and apply over the full recommended case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.
- 3.5 <u>Marking</u>. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in MIL-BUL-103 (see 6.7 herein).

STANDARDIZED
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SIZE <b>A</b>		5962-85010
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Test	Symbol	Conditions 1/ -55°C < To <+125°C	Device type	Group A subgroups	Lin	Unit	
	- Cymison	$-55^{\circ}$ C $\leq$ T <sub>C</sub> $\leq$ +1 $\frac{1}{2}5^{\circ}$ C V <sub>CC</sub> = 5.0 V ±5% unless otherwise specified	1,900	oubgioupo	Min	Max	
Low-level input voltage	V <sub>IL</sub>		01, 02	1,2,3	-0.5		V
High-level input voltage (All except X1 and (RES)	V <sub>IH1</sub>		01, 02	1,2,3	2.0	V <sub>CC</sub> +0.5	V
High-level input voltage at (RES)	V <sub>IH2</sub>		01, 02	1,2,3	3.0	V <sub>CC</sub> +0.5	V
Low-level output voltage	V <sub>OL</sub>	$I_{OL}$ = 2.5 mA for $\overline{SO}$ - $\overline{S2}$ $I_{OL}$ = 2.0 mA for all other outputs	01, 02	1,2,3		0.45	V
High-level output voltage	V <sub>OH</sub>	I <sub>OH</sub> = -400 μA	01, 02	1,2,3	2.4		V
Power supply current	Icc	V <sub>CC</sub> = 5.25 V	01, 02	1,2,3		600	mA
Input leakage current	I <sub>IL</sub>	0 V < V <sub>IN</sub> < V <sub>CC</sub>	01, 02	1,2,3		<u>+</u> 10	μΑ
Output leakage current	l <sub>OL</sub>	0.45V < V <sub>OUT</sub> < V <sub>CC</sub>	01, 02	1,2,3		<u>+</u> 10	μΑ
Low-level clock output voltage	V <sub>CLO</sub>	I <sub>O</sub> = 4.0 mA	01, 02	1,2,3		0.6	V
High-level clock output voltage	V <sub>CHO</sub>	I <sub>O</sub> = -200 μA	01, 02	1,2,3	4.0		٧
Low-level clock input voltage	V <sub>CL1</sub>		01, 02	1,2,3	-0.5	+0.6	V
High-level clock input voltage	V <sub>CH1</sub>		01, 02	1,2,3	3.9	V <sub>CC</sub> +1.0	V
Functional tests		See 4.3.1d	01, 02	7,8			
Input capacitance	C <sub>IN</sub>	See 4.3.1c	01, 02			10	pF
I/O capacitance	C <sub>IO</sub>	See 4.3.1c	01, 02			20	pF

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DEFENSE ELECTRONICS SUPPLY CENTER		REVISION LEVEL	SHEET

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TA	ABLE I. <u>Elec</u>	ctrical performance characteristi	cs - Continu	ed.			
Test	Symbol	Conditions 1/ -55°C < To <+125°C	Device type	Group A subgroups	Lim	nits	Unit
	Cynnoon	Conditions $1/$ -55°C $\leq$ T <sub>C</sub> $\leq$ +125°C V <sub>CC</sub> = 5.0 V ±5% unless otherwise specified	.ypo	casg.caps	Min	Max	
Data in setup (A/D)	t <sub>DVCL</sub>	C <sub>L</sub> = 20 to 200 pF, all	01,02	9,10,11	20		ns
Data in hold (A/D)	t <sub>CLDX</sub>	outputs	01,02	9,10,11	10		ns
Asynchronous ready (ALREADY) active setup time	t <sub>ARYHCH</sub>		01,02	9,10,11	20		ns
AREADY inactive setup time	<sup>t</sup> ARYLCL		01,02	9,10,11	38		ns
AREADY hold time	<sup>t</sup> CHARYX		01,02	9,10,11	15		ns
Synchronous ready (SREADY) transition setup time	<sup>t</sup> SRYCL		01,02	9,10,11	35		ns
SREADY transition hold time	t <sub>CLSRY</sub>		01,02	9,10,11	15		ns
Hold setup 2/	t <sub>HVCL</sub>		01,02	9,10,11	25		ns
INTR, NMI, TEST, TIMERIN setup <u>2</u> /	<sup>t</sup> INVCH		01,02	9,10,11	25		ns
DRQ0, DRQ1, setup	t <sub>INVCL</sub>		01,02	9,10,11	25		ns
Address valid delay	t <sub>CLAX</sub>		01	9,10,11	5	59	ns
			02	9,10,11	5	63	ns
Address hold	t <sub>CLAX</sub>		01	9,10,11	5		ns
			02	9,10,11	5		ns
Address float delay	t <sub>CLAZ</sub>		01	9,10,11	t <sub>CLAX</sub>	35	ns
			02	9,10,11	t <sub>CLAX</sub>	44	ns
Address valid to clock high	t <sub>AVCH</sub>		01,02	9,10,11	10		ns

STANDARDIZED	SIZE <b>A</b>		5962-85010
MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL C	SHEET 5

Test	Symbol	Conditions <u>1/</u> -55°C < T <sub>o</sub> <+125°C	Device type	Group A subgroups	Limits		Unit
, 551	Sysc.	Conditions 1/ -55°C $\leq$ T <sub>C</sub> $\leq$ +125°C $V_{CC} = 5.0 V \pm 5\%$ unless otherwise specified	1,500	ousg.oupo	Min	Max	
Command lines float delay	t <sub>CHCZ</sub>	C <sub>L</sub> = 20 to 200 pF, all outputs	01	9,10,11		45	ns
dolay		outputs	02	9,10,11		56	ns
Command lines valid delay (after float)	<sup>t</sup> CHCV		01	9,10,11		55	ns
			02	9,10,11		76	ns
ALE width	t <sub>LHLL</sub>		01,02	9,10,11	<sup>t</sup> CLCL -35		ns
ALE active delay	t <sub>CHLL</sub>		01	9,10,11		35	ns
			02	9,10,11		44	ns
ALE inactive delay	t <sub>CHLL</sub>		01	9,10,11		35	ns
			02	9,10,11		44	ns
Address hold to ALE inactive	t <sub>LLAX</sub>		01	9,10,11	<sup>t</sup> CHCL -25		ns
			02	9,10,11	t <sub>CHCL</sub>		ns
Data valid delay	t <sub>CLDV</sub>		01	9,10,11	5	44	ns
			02	9,10,11	5	55	ns
Data hold time	t <sub>CLDOX</sub>		01,02	9,10,11	5		ns
Data hold after WR	t <sub>WHDX</sub>		01	9,10,11	<sup>t</sup> CLCL -40		ns
			02	9,10,11	t <sub>CLCL</sub> -50		ns
Control active delay 1	t <sub>CVCTV</sub>		01	9,10,11	5	70	ns
			02	9,10,11	5	87	ns
Control active delay 2	t <sub>CHCTV</sub>		01	9,10,11	5	73	ns
			02	9,10,11	5	76	ns
DEN inactive delay (non-write cycle)	t <sub>CVDEX</sub>		01	9,10,11	10	70	ns
(11011 WING GYOIG)			02	9,10,11	10	87	ns

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MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL C	SHEET 6

	TABLE	I. Electrical performance chara	acteristics - C	ontinued.			_
Test	Symbol	Conditions <u>1/</u> -55°C < T <sub>o</sub> <+125°C	Device type	Group A subgroups	Lim	its	Unit
	- J	Conditions $1/$ -55°C $\leq$ T <sub>C</sub> $\leq$ +125°C V <sub>CC</sub> = 5.0 V $\pm$ 5% unless otherwise specified	3/10	2009.2042	Min	Max	
Address float to RD active	t <sub>AZRL</sub>	C <sub>L</sub> = 20 to 200 pF, all	01,02	9,10,11	0		ns
RD active delay	t <sub>CLRL</sub>	outputs	01	9,10,11	10	70	ns
			02	9,10,11	10	87	ns
RD inactive delay	t <sub>CLRH</sub>		01	9,10,11	10	55	ns
			02	9,10,11	10	76	ns
RD inactive to address active	t <sub>RHAV</sub>		01	9,10,11	<sup>t</sup> CLCL -40		ns
			02	9,10,11	<sup>t</sup> CLCL -50		ns
HLDA valid delay	t <sub>CLHAV</sub>		01,02	9,10,11	5	67	ns
RD width	t <sub>RLRH</sub>		01,02	9,10,11	<sup>2t</sup> CLCL -50		ns
WR	twlwh		01,02	9,10,11	<sup>2t</sup> CLCL -40		ns
Address valid to ALE low	t <sub>AVAL</sub>		01	9,10,11	<sup>t</sup> CLCH -25		ns
			02	9,10,11	<sup>t</sup> CLCH -45		ns
Status active delay	t <sub>CHSV</sub>		01	9,10,11	10	55	ns
			02	9,10,11	10	76	ns
Status inactive delay	<sup>t</sup> CLSH		01	9,10,11	10	65	ns
			02	9,10,11	10	76	ns
Timer output delay	t <sub>CLTMV</sub>	C <sub>L</sub> = 100 pF maximum	01	9,10,11		60	ns
			02	9,10,11		75	ns
Control inactive delay	t <sub>CVCTX</sub>	C <sub>L</sub> = 20 to 200 pF, all	01	9,10,11		55	ns
		outputs	02	9,10,11		76	ns

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MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL C	SHEET 7

TABLE I.	Electrical performance	characteristics	- Continued.
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Test	Symbol	Conditions <u>1</u> / -55°C < T <sub>C</sub> <+125°C	Device type	Group A subgroups	Lim	its	Unit
7 550	Cymbol	$-55^{\circ}$ C $\leq$ T <sub>C</sub> $\leq$ +125 $\circ$ C $\vee$ C $\leq$ 5.0 $\vee$ ±5% unless otherwise specified	1,700	oubgroups	Min	Max	
Reset delay	t <sub>CLRO</sub>	C <sub>L</sub> = 20 to 200 pF, all	01	9,10.11		60	ns
		outputs	02	9,10.11		75	ns
Queue status delay	t <sub>CHQSV</sub>		01	9,10.11		35	ns
			02	9,10.11		44	ns
Chip-select active delay	t <sub>CLCSV</sub>		01	9,10.11	5	66	ns
delay			02	9,10.11	5	80	ns
Chip-select hold from command inactive	tcxcsx		01,02	9,10.11	35		ns
Chip-select inactive delay	<sup>t</sup> CHCSX		01,02	9,10.11	5	47	ns
CLKIN period	t <sub>CKIN</sub>		01	9,10.11	62.5	250	ns
			02	9,10.11	83	250	ns
CLKIN fall time	<sup>t</sup> CKHL	3.5 V to 1.0 V <u>3</u> /	01,02	9,10.11		10	ns
CLKIN rise time	<sup>t</sup> CKLH	1.0 V to 3.5 V <u>3</u> /	01,02	9,10.11		10	ns
CLKIN low time	t <sub>CLCK</sub>	1.5 V <u>3</u> /	01	9,10.11	25		ns
			02	9,10.11	33		ns
CLKIN high time	t <sub>CHCK</sub>	1.5 V <u>3</u> /	01	9,10.11	25		ns
			02	9,10.11	33		ns
CLKIN to CLKOUT skew	t <sub>CICO</sub>	C <sub>L</sub> = 20 to 200 pF, all	01	9,10.11		50	ns
		outputs	02	9,10.11		62.5	ns
CLKOUT period	t <sub>CLCL</sub>		01	9,10.11	125	500	ns
			02	9,10.11	167	500	ns
CLKOUT low time	<sup>t</sup> CLCH	1.5 V <u>3</u> /	01,02	9,10,11	1/2 t <sub>CLCL</sub> -7.5		ns

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SIZE <b>A</b>		5962-85010
	REVISION LEVEL C	SHEET 8

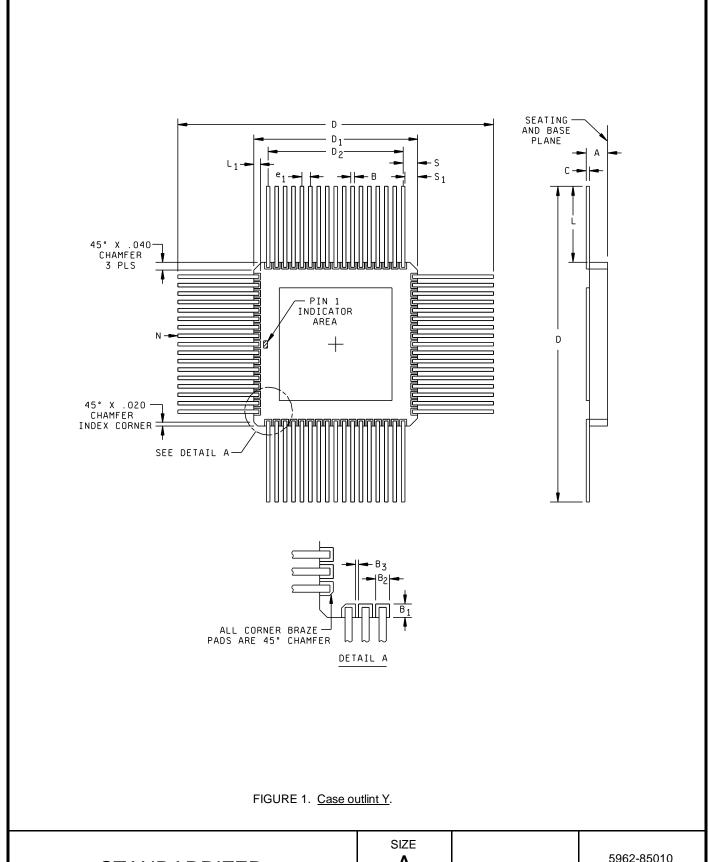
# TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Svmbol	Conditions <u>1</u> / Symbol -55°C ≤ T <sub>C</sub> ≤+125°C		Group A subgroups	Limits		Unit
	- J	Conditions $\frac{1}{2}$ -55°C $\leq$ T <sub>C</sub> $\leq$ +125°C V <sub>CC</sub> = 5.0 V $\pm$ 5% unless otherwise specified	917		Min	Max	
CLKOUT high time	<sup>t</sup> CHCL	1.5 V <u>3</u> /	01,02	9,10.11	1/2 <sup>t</sup> CLCL -7.5		ns
CLKOUT rise time	t <sub>CH1CH2</sub>	1.0 V to 3.5 V <u>3</u> /	01,02	9,10.11		15	ns
CLKOUT fall time	<sup>t</sup> CL2CL1	3.5 V to 1.0 V <u>3</u> /	01,02	9,10.11		15	ns

- 1/ All ac parameters tested as per circuit on figure 4.
- 2/ Setup requirements only to guarantee recognition at next CLK.
- 3/ Voltage indicated refer to voltage measurements on waveforms in figure 4.

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STANDARDIZED	
MILITARY DRAWING	

SIZE <b>A</b>		5962-85010
	REVISION LEVEL C	SHEET 10

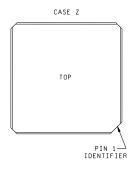
Dimensions				
Ltr	Inches		Millimeters	
	Min	Max	Min	Max
Α	.080	.106	2.03	2.69
В	.016	.020	0.41	0.51
B <sub>1</sub>	.040	.060	1.02	1.52
В2	.030	.040	0.76	1.02
В <sub>3</sub>	.005	.020	0.13	0.51
С	.008	.012	0.20	0.30
D	1.640	1.640 1.870		47.50
D <sub>1</sub>	.935	.970	23.75	24.64
D <sub>2</sub>	.800	BSC	20.32 BSC	
e <sub>1</sub>	.050	BSC	1.27	BSC
L	.375	.450	9.53	11.43
L <sub>1</sub>	.040	.060	1.02	1.52
N	68 PINS		68 F	PINS
S	.66	.087	1.68	2.21
S <sub>1</sub>	.050		1.27	

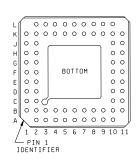
FIGURE 1. Case outline Y - Continued.

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### Case outline Y AD0 AD8 AD1 AD2 AD11 VCC AD4 AD12 AD12 AD13 AD13 6162636465666768 1 2 3 4 5 6 7 8 9 DRQ0 = 60 10 59 DRQ1 □ 11 □ A17/S4 TMR IN 0 □ 58 12 ⊐ A18/S5 TMR IN 1□ 57 13 ⊐ A19/S6 TMR OUT O □ 56 14 ⊐ BHE/S7 TMR OU<u>T 1</u> □ 55 15 ⊐ WR/QS1 <u>RES</u> ⊏ 54 16 ⊐ RD/QSMD PCS0 □ 53 17 ⊐ ALE/QSO V<sub>SS</sub> ⊏ $\neg v_{SS}$ 52 18 PCS1 □ 51 19 → X1 PCS2 □ 50 20 ⊐ X2 PCS3 □ PCS4 □ 49 □ RESET 21 48 22 □ CLKOUT PCS5/A1 C 47 □ ARDY 23 $\begin{array}{c} - \overline{S} \\ \overline{S} \\$ PCS6/A2 □ 46 24 45 25 44 26 $43\,42\,41\,40\,39\,38\,37\,36\,35\,34\,33\,32\,31\,30\,29\,28\,27$ FIGURE 2. Terminal connections.

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# Case outline Z

Symbol	Location	Symbol	Location	Symbol	Location
V <sub>CC</sub> , V <sub>CC</sub>	F1, F11	A16/S3	A2	RD/QSMD	A5
V <sub>SS</sub> , V <sub>SS</sub>	L6, A6	AD15	B1	ARDY	B9
Reset	B8	AD14	C1	SRDY	C11
X1, X2	B7, A7	AD13	D1	LOCK	D10
CLKOUT	A8	AD12	E1	<u>80</u>	A10
RES	L5	AD11	F2	<u>\$1</u>	B10
TEST	D11	AD10	G2	<u>\$2</u>	A9
TMR IN 0	L3	AD9	H2	HOLD	C10
TMR IN 1	К3	AD8	J2	(input)	
TMR OUT 0	L4	AD7	B2	HLDA	B11
TMR OUT 1	K4	AD6	C2	(output)	
DRQ0	L2	AD5	D2	UCS	L10
DRQ1	K2	AD4	E2	LCS	K9
NM1	E10	AD3	G1	MCS0-3	J10, J11, K10, K11
INTO, INT1	E11, F10	AD2	H1	PCS0	K5
INTA2/TNTA0	G10	AD1	J1	PCS1-4	K6, L7, K7, L8
INT3/TNTA1	G11	AD0	K1	PCS5/A1	K8
A19/S6	B4	BHE/S7	A4	PCS6/A2	L9
A18/S5	A3	ALE/QS0	B6	DT/R	H10
A17/S4	B3	WR/QS1	B5	DEN	H11

FIGURE 2. Terminal connections - Continued.

# STANDARDIZED MILITARY DRAWING

SIZE <b>A</b>		5962-85010
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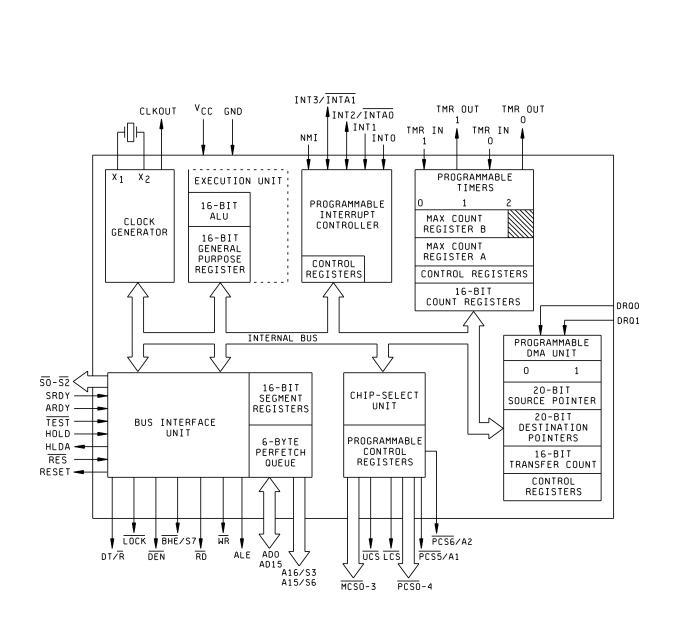


FIGURE 3. Functional block diagram.

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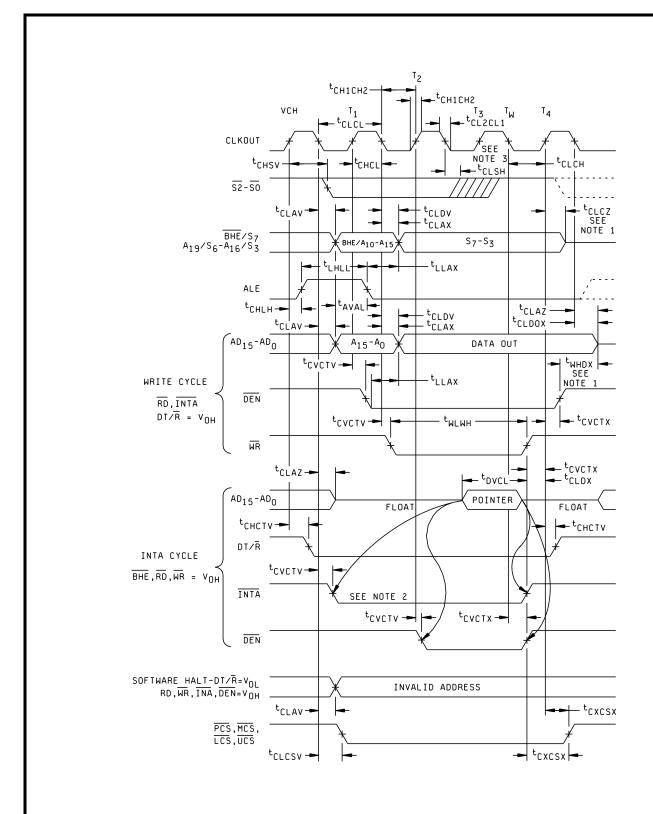
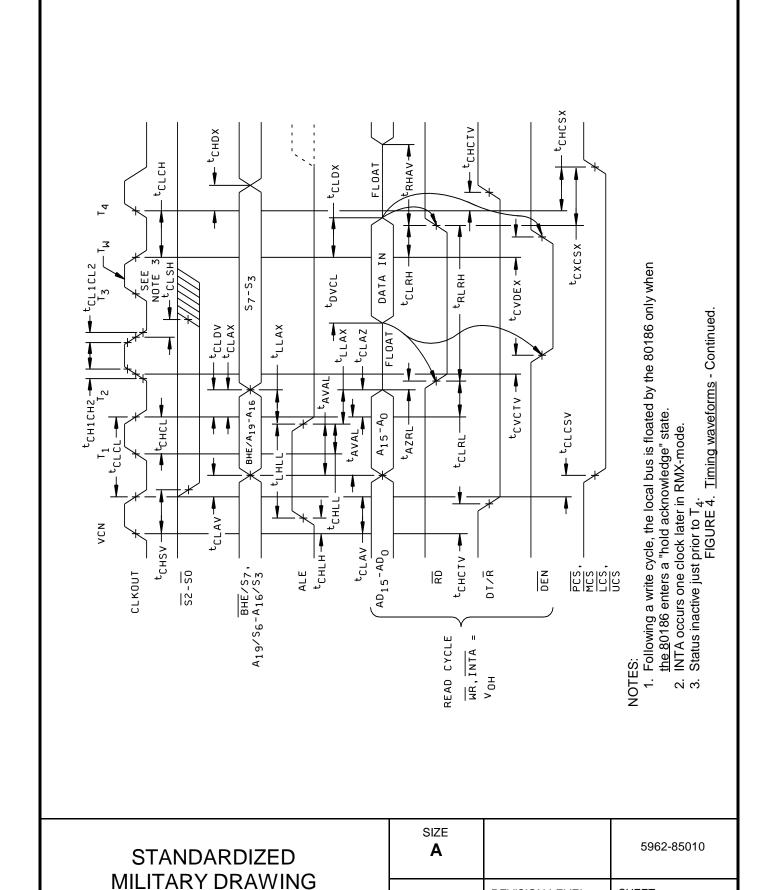


FIGURE 4. Timing waveforms.

# STANDARDIZED MILITARY DRAWING

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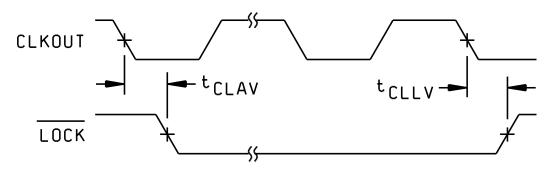
REVISION LEVEL C SHEET

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**DEFENSE ELECTRONICS SUPPLY CENTER** 

DAYTON, OHIO 45444

# BUS LOCK SIGNAL TIMING



# ASYNCHRONOUS SIGNAL RECOGNITION

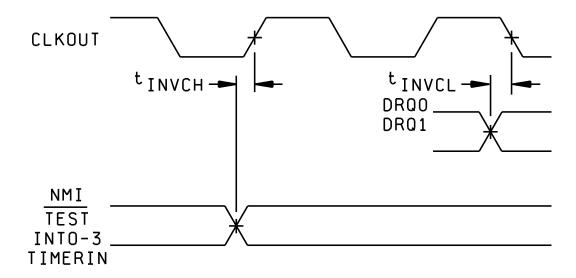
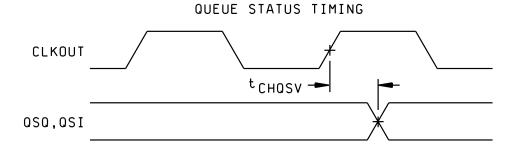
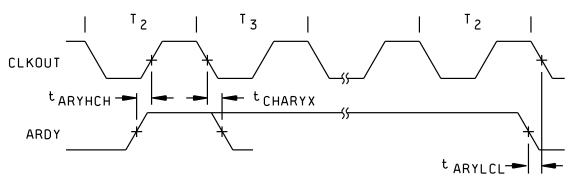


FIGURE 4. Timing waveforms - Continued.

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# SYNCHRONOUS AND ASYNCHRONOUS TIMING



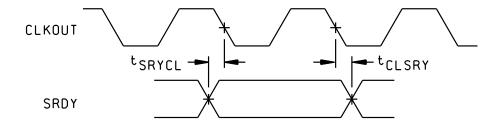


FIGURE 4. Timing waveforms - Continued.

# STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 454444 SIZE A SPECISION LEVEL C SHEET 18

# TIMER TIMING

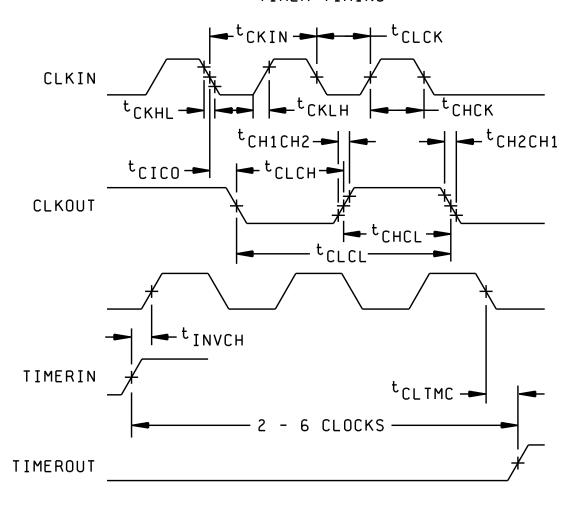


FIGURE 4. Timing waveforms - Continued.

# STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444 SIZE A SIZE A FEVISION LEVEL C SHEET C 19

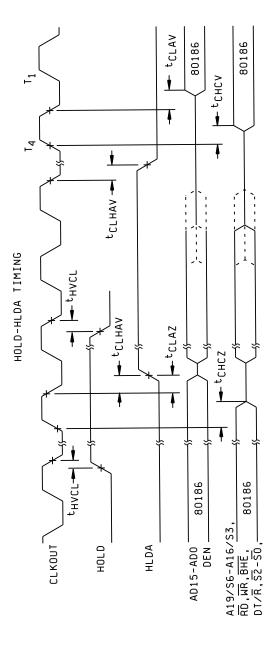


FIGURE 4. Timing waveforms - Continued.

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- 3.6 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7 herein). The certificate of compliance submitted to DESC-ECC prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change</u>. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.9 <u>Verification and review</u>. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
  - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
  - a. Burn-in test, method 1015 of MIL-STD-883.
    - (1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.7 herein).
    - (2)  $T_A = +125^{\circ} \text{ C}$ , minimum.
  - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
  - 4.3.1 Group A inspection.
    - a. Tests shall be as specified in table II herein.
    - b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
    - c. Subgroup 4 (C<sub>IN</sub> and C<sub>IO</sub> measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance. A minimum sample size of five devices with zero rejects shall be required.
    - d. Subgroups 7 and 8, functional testing shall include verification of instruction set (see table III).

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TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Interim electrical parameters (method 5004)	1
Final electrical test parameters (method 5004)	1*, 2, 3, 7, 8, 9, 10, 11
Group A test requirements (method 5005)	1, 2, 3, 4, 7, 8, 9, 10, 11
Groups C and D end-point electrical parameters (method 5005)	2, 8(+125° C), 10

<sup>\*</sup> PDA applies to subgroup 1.

# 4.3.2 Groups C and D inspections.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Steady-state life test conditions, method 1005 of MIL-STD-883.
  - (1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.7 herein).
  - (2)  $T_A = +125^{\circ} C$ , minimum.
  - (3) Test duration: 1,000 hours, except as permitted method 1005 of MIL-STD-883.

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		uction set summary.			
Function	Format			Clock cycles	Comments
DATA TRANSFER MOV = Move:					
Register to register/memory	1000100w	mod reg r/m	<u>]</u>	1/12	Ì
Register/memory to register	1000101w	mod reg r/m	<u>]</u>	2/9	
Immediate to register/memory	1100011w	mod req r/m	data data if W = 1	12-13	8/16-bit
Immediate to register	1011w reg	data	data if W = 1	3-4	8/16-bit
Memory to accumulator	1010000w	addr-low	addr-high	9	
Accumulator to memory	1010001w	addr-low	addr-high	8	
Register/memory to segmet register	10001110	mod 0 reg r/m	]	2/9	
Segment register to register/memory	10001100	mod 0 reg r/m	]	2/11	
PUSH = Push:			_		
Memory	11111111	mod 1 1 0 r/m	<u> </u>	16	
Register	01010 reg		<u> </u>	10	
Segment register	0 0 0 reg 1 1 0			9	
Immediate	011010s 0	data	data if s = 0	10	
PUSHA = Push All	01100000	J			
POP = Pop:		Т	٦		
Memory	10001111	mod 0 0 0 r/m	J	20	
Register	01011 reg	<u>J</u>	7	10	
Segment register	0 0 0 reg 1 1 1	(reg ≠ 01)	J	8	
POPA = Pop All	01100001	J		51	
XCHG = Exchange:		т—	٦		
Register/memory with register	1000011w	mod reg r/m	J	4/17	
Register with accumulator	10010 reg	J		3	
IN = Input from:		T	٦		
Fixed port	1110010w	port	J	10	
Variable port	1110110w	J		8	

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Function	Format	Clock cycles Comment
OUT = Output to:		
Fixed port	1 1 1 0 0 1 1w port	9
Variable port	1110111	7
XLAT = Translate byte to AL	11010111	11
LEA = Load EA to register	10001101 mod reg r/m	6
LDS = Load pointer to DS	1 1 0 0 0 1 0 1 mod reg r/m (mod ± 11)	18
LES = Load pointer to ES	11000100 mod reg r/m (mod ± 11)	18
LAHF = Load AH with flags	10011111	2
SAHF = Store AH into flags	10011110	3
PUSHF = Push flags	10011100	9
POPF = Pop flags	10011101	8
SEGMENT = Segment Override:		2
CS	00101110	2
DS	00110110	2
ES	00100110	2
ARITHMETIC		
ADD = Add:	22222	
Reg/memory with register to either	0 0 0 0 0 0 d w   mod reg r/m	3/10
Immediate to register/memory	100000sw mod 000 r/m data data if s	<u>w = 01</u> 4/16
Immediate to accumulator	0 0 0 0 0 1 0 w data data if w = 1	3/4 8/16-bit
ADC = Add with carry:		
Reg/memory with register to either	0 0 0 1 0 0 d w mod reg r/m	3/10
Immediate to register/memory	100000sw mod 010 r/m data data if s	w = 01 4/16
Immediate to accumulator	0 0 0 1 0 1 0 w data data if w = 1	3/4 8/16-bit
INC = Increment:		_
Register/memory	1111111 w mod 0 0 0 r/m	3/15
Register	01000 reg	3

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Immediate from accumulator  SSB = Subtract with borrow:  Reg/memory and register to either  Immediate from register/memory  Immediate from accumulator  DEC = Decrement:  Register/memory  Register  CMP = Compare:  Register/memory with register  Register with register/memory  Register with register/memory  Register with register/memory  Register/memory  Register/memory with register  Register/memory with register  Register/memory  Register/memory  Register/memory with register  Register/memory  Register/memory  Register/memory  Register/memory  Register/memory  Register/memory  Register/memory  Register/memory	Clock cycles
Reg/memory and register to either  Immediate from register/memory  Immediate from accumulator  SSB = Subtract with borrow:  Reg/memory and register to either  Immediate from register/memory  Reg/memory and register to either  Immediate from register/memory  Immediate from register/memory  Immediate from accumulator  DEC = Decrement:  Register/memory  Interval 100000 w mod 101 r/m data data if w = 1  DEC = Decrement:  Register/memory  Interval 100000 w mod req r/m  Immediate from accumulator  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from accumulator  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from accumulator  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 100000 w mod req r/m  Interval 100000 w mod req r/m  Immediate from register/memory  Interval 10000 w mod req r/m  Immediate from register/memory  Interval 10000 w mod req r/m  Interval 10000 w mod	3/4 8/16-bit  3/4 8/16-bit  3/4 8/16-bit  3/10 4/16 3/4 8/16-bit  3/15
Immediate from register/memory  Immediate from accumulator  SSB = Subtract with borrow:  Reg/memory and register to either  Immediate from accumulator  Immediate from register/memory  Immediate from register/memory  Immediate from accumulator  DEC = Decrement:  Register/memory  Register  CMP = Compare:  Register/memory with register  Register with register/memory  Register with register/memory  In 0 0 0 0 0 w mod 1 0 1 r/m data data if w = 1  O 0 1 1 1 0 d w mod req r/m  O 0 0 1 1 1 0 w data data if w = 1  O 0 1 1 1 0 w mod 0 0 1 r/m  O 1 0 0 1 reg  O 1 1 1 0 1 w mod req r/m  O 0 1 1 1 0 0 w mod req r/m	3/4 8/16-bit  3/4 8/16-bit  3/4 8/16-bit  3/10 4/16 3/4 8/16-bit  3/15
Immediate from accumulator  SSB = Subtract with borrow:  Reg/memory and register to either  Immediate from register/memory  Immediate from accumulator  DEC = Decrement:  Register/memory  Register  CMP = Compare:  Register/memory with register  Register with register/memory  O 0 1 1 1 0 w mod req r/m  1 0 0 0 0 0 s w mod 0 1 1 r/m data data if w = 1  O 0 1 1 1 0 w mod 0 0 1 r/m  O 1 0 0 1 reg  O 1 1 1 0 w mod req r/m  O 1 1 1 0 w mod req r/m	3/4 8/16-bit  3/10  4/16  3/4 8/16-bit  3/15
Reg/memory and register to either  Immediate from register/memory  Immediate from accumulator  DEC = Decrement:  Register/memory  Register  CMP = Compare:  Register/memory with register  Register with register/memory  Register/memory  Register/memory with register  Register/memory	3/10 4/16 $3/4$ 8/16-bit
Reg/memory and register to either  Immediate from register/memory  Immediate from accumulator  DEC = Decrement:  Register/memory  Register  CMP = Compare:  Register/memory with register  Register with register/memory  O 0 1 1 1 0 d w mod req r/m  1 0 0 0 0 5 w mod 0 1 1 r/m data data if w = 1  O 0 1 1 1 0 w data data if w = 1  O 1 1 1 1 1 1 1 w mod 0 0 1 r/m  O 1 1 1 1 1 1 1 w mod 0 0 1 r/m  O 1 1 1 1 1 1 1 w mod req r/m  O 0 1 1 1 0 0 w mod req r/m	4/16 3/4 8/16-bit 3/15
Immediate from register/memory  Immediate from accumulator  Immediate from register/memory  Immediate from accumulator  Immediate from accumulator	4/16 3/4 8/16-bit 3/15
mmediate from accumulator         0 0 0 1 1 1 0 w         data         data if w = 1           DEC = Decrement:         Register/memory         1 1 1 1 1 1 1 w         mod 0 0 1         r/m           CMP = Compare:         Register/memory with register         0 0 1 1 1 0 1 w         mod reg         r/m           Register with register/memory         0 0 1 1 1 0 0 w         mod reg         r/m	3/4 8/16-bit 3/15
DEC = Decrement:  Register/memory  Register  0 1 0 0 1 reg  CMP = Compare:  Register/memory with register  0 0 1 1 1 0 1 w mod reg r/m  0 0 1 1 1 0 0 w mod reg r/m	3/15
Register/memory  1111111 w mod 0 0 1 r/m  01001 reg  CMP = Compare:  Register/memory with register  0011101 w mod reg r/m  0011100 w mod reg r/m	
Register  O 1 0 0 1 reg  CMP = Compare:  Register/memory with register  O 0 1 1 1 0 1 w mod reg r/m  O 0 1 1 1 0 0 w mod reg r/m	
CMP = Compare:  Register/memory with register  0 0 1 1 1 0 1 w mod req r/m  0 0 1 1 1 0 0 w mod req r/m	3
Register/memory with register    0 0 1 1 1 0 1 w   mod req r/m	
Register with register/memory 0 0 1 1 1 0 0 w mod reg r/m	
	3/10
mmediate with register/memory 100000sw mod 111 r/m data dat	3/10
	a if s w = 01 3/10
mmediate with accumulator 0 0 1 1 1 1 0 w data data if w = 1	3/4 8/16-bit
NEG = Change sign	3
AAA = ASCII adjust for add	8
DAA = Decimal adjust for add  00100111	4
AAS = ASCII adjust for subtract 0 0 1 1 1 1 1 1	7
DAS = Decimal adjust for substract 0 0 1 0 1 1 1 1	4
MUL = Multiply (unsigned):	
Register-Byte Register-Word Memory-Byte Memory-Word	26-28 35-37 32-34 41-43
IMUL = Integer multiply (signed): 1111011 w mod 101 r/m	
Register-Byte Register-Word Memory-Byte Memory-Word	25-28 34-37 31-34 40-43

Function	Format						Clock cycles	Comments
ARITHMETIC (Continued):								
IMUL = Integer immediate multiply	011010s1	mod reg	r/m	dat	data if s	s = 0	22-25/	
(signed)							29-32	
				7				
DIV = Divide (unsigned):	1111011w	mod 1 1	0 r/m					
Register-Byte register-Word Memory-Byte Memory-Word							29 38 35 44	
IDIV = Integer divide (signed):	1111011w	mod 1 1	1 r/m	]				
Register-Byte Register-Word Memory-Byte Memory-Word							44-52 53-61 50-58 59-67	
AAM = ASCII adjust for multiply	11010100	0000	1010	]			19	
AAD = ASCII adjust for divide	11010101	0000	1010	]			15	
CBW = Convert byte to word	10011000						2	
CWD = Convert word to double word	10011001						4	
LOGIC								
Shift/rotate instructions:	·			_				
Register/memory by 1	1101000w	mod TT	T r/m	╛			2/15	
Register/memory by CL	1101001w	mod TT	T r/m				5+n/ 17+n	
Register/memory by count	1100000w	mod TT	T r/m	cc	unt	]	5+n/ 17+n	
						_		
		TT 0 0 0 0 0 1 0 1 0 0 1 1 1 0 0 1 0 1	RÖR RCL RCR SHL/SA SHR					
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Function	Formet			Clasti	Commercial
Function	Format			Clock cycles	Comments
AND = And:					
Reg/memory and register to either	001000dw mod re	g r/m		3/10	
Immediate to register/memory	1000000 w mod 1	0 0 r/m data	a data if w = 1	4/16	
Immediate to accumulator	0010010w	data data	a if w = 1	3/4	8/16-bit
TEST = And function to flags,					
no result:					
Register/memory and register	1000010w mod re	g r/m		3/10	
Immediate data and register/memory	1111011w mod 0	0 0 r/m data	data if w = 1	4/10	
Immediate data and accumulator	1010100w c	lata data	a if w = 1	3/4	8/16-bit
OR = Or:					
Reg/memory and register to either	000010dw mod re	g r/m		3/10	
Immediate to register/memory	100000w mod 0	0.1 r/m data	a data if w = 1	4/16	
Immediate to accumulator	0000110w c	lata data	a if w = 1	3/4	8/16-bit
XOR = Exclusive or:					
Reg/memory and register to either	0 0 1 1 0 0 d w mod re	g r/m		3/10	
Immediate to register/memory	1000000w mod 1	1 0 r/m data	a data if w = 1	4/16	
Immediate to accumulator	0011010w	data data	a if w = 1	3/4	8/16-bit
NOT = Invert register/memory	1111011w moc 0	1 0 r/m		3	
STRING MANIPULATION:					
MOVS = Move byte/word	1010010w			14	
CMPS = Compart byte/word	1010011w			22	
SCAS = Scan byte/word	1010111w			15	
LODS = Load byte/wd to AL/AX	1010110w			12	
STOS = Store byte/wd from AL/A	1010101w			10	
INS = input byte/wd from DX port	0110110w			14	
OUTS = Output byte/wd to DX port	0110111w			14	
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Function	Format			Clock cycles	Comments
STRING MANIPULATION (Continued): Repeated by count in CX					
MOVS = Move string	11110010	1010010w	]	8+8n	İ
CMPS = Compare string	1111001z	1010011w		5+22n	
SCAS = Scan string	1111001z	1010111w	]	5+15n	
LODS = Load string	11110010	1010110w	]	6+11n	
STOS = Store string	11110010	1010101w	]	6+9n	
INS = Input string	11110010	0110110w	]	8+8n	
OUTS = Output str9ng	11110010	0110111w	]	8+8n	
CONTROL TRANSFER					
CALL = Call:					
Direct within segment	11101000	disp-low c	disp-high	14	
Register/memory indirect within segment	11111111	mod 0 1 0 r/m	J	13/19	
Direct intersegment	10011010	segment offset		23	
		segment selecto	r		
Indirect intersegment	11111111	mod 0 1 1 r/m	]	38	
JMP = Unconditional jump:					
Short/long	11101011	disp-low		13	
Direct within segment	11101001	disp-low	disp-high	13	
Register/memory indirect within	11111111	mod 1 0 0 r/m	]	11/17	
segment			,		
Direct intersegment	11101010	segment offset		13	
		segment selecto	r		
Indirect intersegment	11111111	mod 1 0 1 r/m	]	26	
RET = Return from CALL:					
Within segment	11000011	]		16	
Within seg adding immed to SP	1100010	data-low	data-high	18	
Intersegment	11001011	J		22	
Intersegment adding immediate to SP	11001010	data-low	data-high	25	

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Function	Format			Clock cycles	Comments
CONTROL TRANSFER (Continued):					
JE/JZ = Jump on equal zero	01110100 disp			4/13	JMP not
JL/JNGE = Jump on less/not greater or equal	01111100 disp			4/13	taken/JMP taken
JLE/JNG = Jump on less or equal/ not greater	01111110 disp			4/13	
JB/JNAE = Junp on below/not above or equal	01110010 disp			4/13	
JBE/JNA = Jump on below or equal/not above	01110110 disp			4/13	
JP/JPE = Jump on parity/parity even	01111010 disp			4/13	<u> </u>
JO = Jump on overflow	01110000 disp		İ	4/13	- -
JS = Jump on sign	01111000 disp			4/13	
JNE/JNZ = Jump on not equal/ not zero	01110101 disp			4/13	
JNL/JGE = Jump on not less/ greater or equal	01111101 disp			4/13	
JNLE/JG = Jump on not less or equal/greater	01111111 disp			4/13	
JNB/JAE = Jump on not below/ above or equal	01110011 disp			4/13	
JNBE/JA = Jump on not below/ or equal/above	01110111 disp			4/13	
JNP/JPO = Jump on not par/par odd	01111011 disp			4/13	
JNO = Jump on not overflow	01110001 disp			4/13	
JNS = Jump on not sign	01111001 disp			4/13	
JCXZ = Jump on CX zero	11100011 disp			5/15	
LOOP = Loop CX times	11100010 disp	╛		6/16	
LOOPZ/LOOPE = Loop while zero/ equal	11100001 disp			6/16	LOOP not taken/LOOP taken
LOOPNZ/LOOPNE = Loop while not zero/equal	11100000 disp		-	6/16	
zero/equal STANDARE	DIZED	SIZE <b>A</b>			5962-85010
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Function	Format				Clock cycles	Comments
ENTER = Enter procedure	11001000	data-low d	ata-high	L		
L = 0					15	
L = 1					25	Ī
L>1					22+16 (n-1)	
LEAVE = Leave procedure	11001001				8	
INT = Interrupt:						
Type specified	11001101	type			47	:# INIT
Type 3	11001100				45	if INT. taken/ if INT.
INTO = Interrupt on overflow	11001110				48/4	not taken
IRET = Interrupt return	11001111				28	
BOUND = Detect value out of range	01100010	mod reg r/m			33-35	
PROCESSOR CONTROL		ı				
CLC = Clear carry	11111000				2	
CMC = Complement carry	11110101				2	
STC = Set carry	11111001				2	
CLD = Clear direction	11111100				2	  - 
STD = Set direction	11111101				2	
CLI = Clear interrupt	11111010				2	
STI = Set interrupt	11111011				2	
HLT = Halt	11110100				2	
WAIT = Wait	10011011				6	if test = 0
LOCK = Bus lock prefix	11110000				2	
ESC = Processor extension escape	10011TTT	mod LLL	r/m	]	6	

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### NOTES:

The effective address (EA) of the memory operand is computed according to the mod and r/m fields:

if mod = 11 then r/m is treated as a REG field

if mod = 00 then DISP = 0\*, disp-low and disp-high are absent

if mod = 01 then DISP = disp-low sign-extended to 16-bits, disp-high is absent

if mod = 10 then DISP = disp-high: disp-low

if r/m = 000 then EA = (BX) + (SI) + DISP

if r/m = 001 then EA = (BX) + (DI) + DISP

if r/m = 010 then EA = (BP) + (SI) + DISP

if r/m = 011 then EA = (BP) + (DI) + DISP

if r/m = 100 then EA = (SI) + DISP

if r/m = 101 then EA = (DI) + DISP

if r/m = 110 then EA = (BP) + DISP\*

if r/m = 111 then EA = (BX) + DISP

DISP follows 2nd byte of instruction (before data if required)

\*Except if mod = 00 and r/m = 110 then EA = disp-high: disp-low.

EA calculation time is 4 clock cycles for all modes, and is included in the execution times given whenever appropriate.

SEGMENT OVERRIDE PREFIX

reg is assigned according to the following:

reg	Segment Register
00	ES
01	CS
10	SS
11	DS

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### NOTES - Continued.

REG is assigned according to the following table:

 $\begin{array}{cccc} 16\text{-Bit}(w=1) & 8\text{-Bit}(w=0) \\ & 000 \text{ AX} & 000 \text{ AL} \\ 001 \text{ CX} & 001 \text{ CL} \\ 010 \text{ DX} & 010 \text{ DL} \\ 011 \text{ BX} & 011 \text{ BL} \\ 100 \text{ SP} & 100 \text{ AH} \\ 101 \text{ BP} & 101 \text{ CH} \\ 110 \text{ SI} & 110 \text{ DH} \\ 111 \text{ DI} & 111 \text{ BH} \end{array}$ 

The physical addresses of all operands addressed by the BP register are computed using the SS segment register. The physical addresses of the destination operands of the string primitive operations (those addressed by the DI register) are computed using the ES segment, which may not be overridden.

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- 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.
- 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
- 6.2 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.4 <u>Symbols, definitions, and functional descriptions</u>. The symbols, definitions, and functional descriptions for this device shall be as follows:

Symbol Name and function System power: +5 volt power supply.  $V_{CC}$ System ground.  $V_{SS}$ Reset output indicates that the 80186 CPU is being reset, and can be used as a system reset. It is active HIGH, synchronized with the processor clock, and lasts an integer number of clock periods corresponding to the length of the RES signal. RESET Crystal inputs, X1 and X2, provide an external connection for a fundamental mode parallel resonant crystal for the internal crystal oscillator. X1 can interface to an X1, X2 external clock instead of a crystal. In this case, minimize the capacitance on X2 or drive X2 with complemented X1. The input or oscillator frequency is internally divided by two to generate the clock signal (CLKOUT). Clock output provides the system with a 50 percent duty cycle waveform. All device pin timings are specified relative to CLKOUT. **CLKOUT** System reset causes the 80186 to immediately terminate its present activity, clear the internal logic, and enter a dormant state. This signal may be asynchronous to the 80186 clock. The 80186 begins fetching instructions approximately 7 clock cycles after RES is returned HIGH. RES is required to be LOW for greater than 4 clock cycles and is internally synchronized. For proper initialization, the LOW-to-HIGH transition of RES must occur no sooner than 50 microseconds after power up. RES

This input is provided with a Schmitt-tr igger to facilitate power-on RES generation via an RC network. When RES occurs, the 80186 will drive the status lines to an inactive level for one clock, and then three-state them.

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**TEST** 

TEST is examined by the WAIT instruction. If the TEST input is HIGH when "WAIT" execution begins, instruction execution will suspend. TEST will be resampled until it goes LOW, at which time execution will resume. If interrupts are enabled while the 80186 is waiting for TEST, interrupts will be serviced. The input is a waiting to the state of

is synchronized internally.

Timer inputs are used either as clock or control signals, depending upon the programmed timer mode. These inputs are active HIGH (or LOW-to-HIGH transi-TMR IN 1

tions are counted) and internally synchronized.

TMR OUT 0, Timer outputs are used to provide single pulse or continuous waveform gener-

TMR OUT 1 ation, depending upon the timer mode selected.

DRQ0 DRQ1 DMA request is driven HIGH by an external device when it desires that a DMA channel (channel 0 or 1) perform a transfer. These signals are active HIGH, level-triggered, and internally synchronized.

NMI

Non-maskable interrupt is an edge-triggered input which causes a type 2 interrupt. NMI is not maskable internally. A transition from a LOW to HIGH initiates the interrupt at the next instruction boundary. NMI is latched internally. An NMI duration of one clock or more will guarantee service. This input is internally synchronized.

Maskable interrupt requests can be requested by strobing one of these pins. When configured as inputs, these pins are active HIGH. Interrupt requests are synchronized internally. INT2 and INT3 may be configured via software to provide active-LOW interrupt-acknowledge output signals. All interrupt inputs may be configured via software to be either edge-or level-triggered. To ensure recognition, all interrupt requests must remain active until the interrupt is INT0, INT1, INT2/INTA0 INT3/INTA1

acknowleged. When iRMX mode is selected, the function of these pins changes.

Address bus outputs (16-19) and bus cycle status (3-6) reflect the four most significant address bits during  $T_1$ . These signals are active HIGH. During  $T_2$ ,  $T_3$ ,  $T_W$ , and  $T_4$ , status information is available on these lines as encoded below: A19/S6, A18/S5, A17/S4,

A16/S3

	Low	High
S6	Processor cycle	DMA cycle

S3, S4, and S5 are defined as LOW during T<sub>2</sub>-T<sub>4</sub>.

 $AD_{15}$ - $AD_0$ 

Address/data bus (0-15) signals constitute the time multiplexed memory or I/O address (T<sub>1</sub>) and data (T<sub>2</sub>, T<sub>3</sub>, T<sub>W</sub>, and T<sub>4</sub>) bus. The bus is active HIGH A<sub>0</sub> is analogous to BHE for the lower byte of the data bus, pins D<sub>7</sub> through D<sub>0</sub>. It is LOW during T<sub>1</sub> when a byte is to be transferred onto the lower portion of the bus in memory of I/O operations.

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BHE/S7

During T<sub>1</sub> the bus high enable signal should be used to determine if data is to be enabled onto the most significant half of the data bus, pins  $D_{15}$ - $D_{8}$ .  $\overline{BHE}$  is LOW during T<sub>1</sub> for read, write, and interrupt acknowledge cycles when a byte is to be transferred on the higher half of the bus. The S7 status information is available during T<sub>2</sub>, T<sub>3</sub>, and T<sub>4</sub>. S7 is logically equivalent to  $\overline{BHE}$ . The signal is active LOW, and is three-stated OFF during bus HOLD.

BHE and AO encodings			
BHE value	AO value	Function	
0	0	Word transfer Byte transfer on upper half of data bus	
1	0	(Ď15-D8)  Byte transfer on lower half of data bus	
1	1	Reserved	

ALE/QS0

Address latch enable/queue status 0 is provided by the 80186 to latch the address into the address latches. ALE is active HIGH. Addresses are guaranteed to be valid on the trailing edge of ALE. The ALE rising edge is generated off the rising edge of the CLKOUT immediately preceding  $\mathsf{T}_1$  of the associated bus cycle. The trailing edge is generated off the CLKOUT rising edge in  $\mathsf{T}_1$ . Note that ALE is never floated.

WR/QS1

Write strobe/queue status 1 indicates that the data on the bus is to be written into a memory or an I/O device.  $\overline{WR}$  is active for  $T_2$ ,  $T_3$ , and  $T_W$  of any write cycle. It is active LOW, and floats during "HOLD." It is driven HIGH for one clock during reset, and then floated. When the 80186 is in queue status mode, the ALE/QS0 and  $\overline{WR}$ /QS1 pins provide information about processor instruction queue interaction.

QS1	QS2	Queue operation
0 0 1 1	0 1 1 0	No queue operation First opcode byte fetched from the queue Subsequent byte fetched from the queue Empty the queue

RD/QSMD

Read strobe indicates that the 80186 is performing a memory or I/O read cycle.  $\overline{RD}$  is active LOW for  $T_2,\,T_3,\,$  and  $T_W$  of any read cycle. It is guaranteed not to go LOW in  $T_2$  until after the address bus is floated.  $\overline{RD}$  is active LOW, and floats during "HOLD."  $\overline{RD}$  is driven HIGH for one clock during reset, and then the output driver is floated. A weak internal pull-up mechanism on the  $\overline{RD}$  line holds it HIGH when the line is not driven. During RESET the pin is sampled to determine whether the 80186 should provide ALE, WR, and RD, or if the queue-status should be provided.  $\overline{RD}$  should be connected to GND to provide queue-status data.

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**ARDY** 

Asynchronous ready informs the 80186 that the addressed memory space or I/O device will complete a data transfer. The ARDY input pin will accept an asynchronous input, and is active HIGH. Only the rising edge is internally synchronized by the 80186. This means that the falling edge of ARDY must be synchronous ready (ARDY) or synchronous ready (ARDY) must be active to terminate a bus cycle.

terminate a bus cycle.

Synchronous ready must be synchronized externally to the 80186. The use of SRDY **SRDY** 

provides a relaxed system-timing specification on the ready input. This is accomplished by eliminating the one-half clock cycle which is required for internally resolving the signal level when using the ARDY input. This line is active HIGH. If this line is connected to V<sub>CC</sub>, no WAIT states are inserted. Asynchronous ready (ARDY) or synchronous ready (SRDY) must be active before a bus cycle is terminated. If unused, this line should be tied LOW.

**LOCK** 

LOCK output indicates that other system bus masters are not to gain control of the system bus while LOCK is active LOW. The LOCK signal is requested by the LOCK prefix instruction and is activated at the beginning of the first data cycle associated with the instruction following the LOCK prefix. It remains active until the completion of the instruction following the LOCK prefix. No prefetches will occur while LOCK is asserted. LOCK is active LOW, is driven HIGH for one clock during RESET, and then floated. If unused, this line should be tied LOW.

S0, S1, S2 Bus cycle status \$\overline{S0}\$-\$\overline{S2}\$ are encoded to provide bus-transaction information.

80186 bus cycle status information			
<u>82</u>	S1	<u>80</u>	Bus cycle initiated
0 0 0 0 1 1 1 1	0 0 1 1 0 0 1	0 1 0 1 0 1	Interrupt acknowledge Read I/O Write I/O Halt Instruction fetch Read data from memory Write data to memory Passive (no bus cycle)

The status pins float during "HOLD."

 $\overline{S2}$  may be used as a logical M/IO indicator, and  $\overline{S1}$  as a DT/R indicator.

The status lines are driven HIGH for one clock during reset, and then floated until a bus cycle begins.

HOLD (input) HLDA (output) HOLD indicates that another bus master is requesting the local bus. The HOLD input is active HIGH. HOLD may be asynchronous with respect to the 80186 clock. The 80186 will issue a HLDA (HIGH) in response to a HOLD request at the end of T<sub>4</sub> or T<sub>1</sub>. Simultaneous with the issuance of HLDA the 80186 will float the local bus and control lines. After HOLD is detected as being LOW, the 80186 will lower HLDA. When the 80186 needs to run another bus cycle, it will again drive the local bus and control lines.

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Upper memory chip select is an active LOW output whenever a memory reference is made to the defined upper portion (1K-256K block) of memory. This line is not floated during bus HOLD. The address range activating UCS is software **UCS** programmable. Lower memory chip select is active LOW whenever a memory reference is made to the defined lower portion (1K-256K) of memory. This line is not floated during bus HOLD. The address range activating  $\overline{\text{LCS}}$  is software programmable. LCS Mid-range memory chip select signals are active LOW when a memory reference is made to the defined mid-range portion of memory (8K-512K). These lines are not floated during bus HOLD. The address ranges activating MCS0-3 are software MCS<sub>0</sub>-3 programmable. Peripheral chip select signals 0-4 are active LOW when a reference is made to the defined peripheral area (64K byte I/O space). These lines are not floated during bus HOLD. The address ranges activating PCS 0-4 are software PCS<sub>0</sub> PCS<sub>1</sub>-4 Peripheral chip select 5 or latched A $_1$  may be programmed to provide a sixth peripheral chip select, or to provide an internally latched A $_1$  signal. The address range activating PCS5 is software programmable. When programmed to provide latched A $_1$ , rather than PCS5, this pin will retain the previously latched value of A $_1$  during a bus HOLD. A $_1$  is active HIGH. PCS5/A1 Peripheral chip select 6 or latched  $A_2$  may be programmed to provide a seventh eripheral chip select, or to provide an internally latched  $A_2$  signal. The address range activating  $\overline{PCS6}$  is software programmable. When programmed to provide latched  $A_2$ , rather than  $\overline{PCS6}$ , this pin will retain the previously latched value of  $A_2$  during a bus HOLD.  $A_2$  is active HIGH. PCS6/A2 Data transmit/receive controls the direction of data flow through the external data bus transceiver. When LOW, data is transferred to the 80186. When HIGH the 80186 places write data on the data bus. DT/R DEN Data enable is provided as a data bus transceiver output enable. DEN is active LOW during each memory and I/O access. DEN is HIGH whenever DT/R changes

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- 6.5 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6022.
- 6.6 <u>Comments</u>. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone (513) 296-5375.
- 6.7 <u>Approved sources of supply.</u> Approved sources of supply are listed in MIL-BUL-103. Additional sources will be added to MIL-BUL-103 as they become available. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.7) has been submitted to and accepted by DESC-ECS. The approved sources of supply listed below are for information purposes only and are current only to the date of the last action of this document.

Military drawing part number	Vendor CAGE number	Vendor similar part number <u>1</u> /
8501001ZX	34649 34335	MG80186-8/B 80186/BZC
8501001YX	34649	MQ80186-8/B
8501002ZX	34649	MG80186-6/B 80186-6/BZC
8501002YX	34335	MQ80186-6/B

1/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGEVendor namenumberand address

34335 Advanced Micro Devices 901 Thompson Place

901 Thompson Place P.O. Box 3453 Sunnyvale, CA 94081

34649 Intel Corporation 3065 Bowers Auenue Santa Clara, CA 95051

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